PEMH19; PUMH19

NPN/NPN resistor-equipped transistors; R1 = 22 k Ω , R2 = open

Rev. 03 — 15 November 2009

Product data sheet

1. Product profile

1.1 General description

NPN/NPN Resistor-Equipped Transistors (RET).

Table 1. Product overview

Type number	Package		NPN/PNP	PNP/PNP
	NXP	JEITA	complement	complement
PEMH19	SOT666	-	PEMD19	PEMB19
PUMH19	SOT363	SC-88	PUMD19	PUMB19

1.2 Features

- Built-in bias resistor
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs

1.3 Applications

- Low current peripheral driver
- Control of IC inputs
- Replaces general-purpose transistors in digital applications

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	50	V
Io	output current (DC)		-	-	100	mA
R1	bias resistor 1 (input)		15.4	22	28.6	kΩ



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NPN/NPN resistor-equipped transistors; R1 = 22 k Ω , R2 = open

Pinning information 2.

Table 3. **Pinning**

	9		
Pin	Description	Simplified outline	Symbol
1	GND (emitter) TR1		
2	input (base) TR1	6 5 4	6 5 4
3	output (collector) TR2		
4	GND (emitter) TR2		TR2
5	input (base) TR2		TR1
6	output (collector) TR1	001aab555	
			1 2 3
			sym090

Ordering information 3.

Table 4. **Ordering information**

Type number	Package		
	Name	Description	Version
PEMH19	-	plastic surface mounted package; 6 leads	SOT666
PUMH19	SC-88	plastic surface mounted package; 6 leads	SOT363

Marking 4.

Product data sheet

Table 5. **Marking codes**

Type number	Marking code ^[1]
PEMH19	6F
PUMH19	H6*

^{[1] * = -:} made in Hong Kong

^{* =} p: made in Hong Kong

^{* =} t: made in Malaysia

^{* =} W: made in China

5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per transis	stor				
V_{CBO}	collector-base voltage	open emitter	-	50	V
V_{CEO}	collector-emitter voltage	open base	-	50	V
V_{EBO}	emitter-base voltage	open collector	-	5	V
Io	output current (DC)		-	100	mA
I _{CM}	peak collector current		-	100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$			
	SOT363		<u>[1]</u> -	200	mW
	SOT666		[1][2] -	200	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
Per device)				
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$			
	SOT363		<u>[1]</u> -	300	mW
	SOT666		[1][2]	300	mW

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	sistor					
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air				
	SOT363		<u>[1]</u> -	-	625	K/W
	SOT666		[1][2] _	-	625	K/W
Per device	ce					
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air				
	SOT363		<u>[1]</u> -	-	416	K/W
	SOT666		[1][2]	-	416	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

^[2] Reflow soldering is the only recommended soldering method.

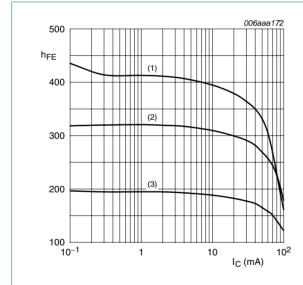
^[2] Reflow soldering is the only recommended soldering method.

7. Characteristics

Table 8. Characteristics

 $T_{amb} = 25 \, ^{\circ}\text{C}$ unless otherwise specified.

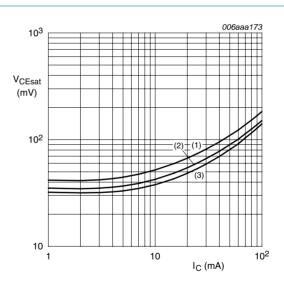
ranib — = 0	e amose ome wee ope					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	istor					
I _{CBO}	collector-base cut-off current	$V_{CB} = 50 \text{ V}; I_E = 0 \text{ A}$	-	-	100	nA
I _{CEO}	collector-emitter	$V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A}$	-	-	1	μΑ
	cut-off current	$V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A};$ $T_{j} = 150 ^{\circ}\text{C}$	-	-	50	μА
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}$	-	-	100	nA
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 1 \text{ mA}$	100	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$	-	-	150	mV
R1	bias resistor 1 (input)		15.4	22	28.6	kΩ
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	-	-	2.5	pF





- (1) $T_{amb} = 100 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -40 \, ^{\circ}C$

Fig 1. DC current gain as a function of collector current; typical values

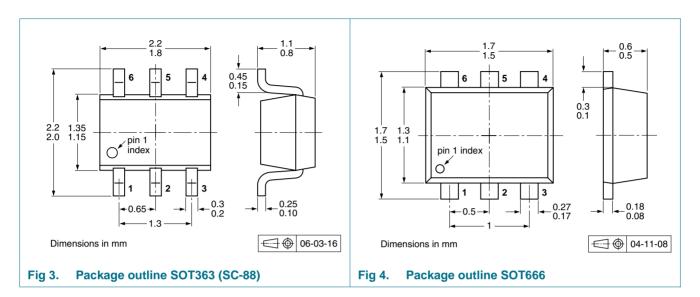


 $I_{\rm C}/I_{\rm B} = 20$

- (1) $T_{amb} = 100 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -40 \, ^{\circ}C$

Fig 2. Collector-emitter saturation voltage as a function of collector current; typical values

8. Package outline



9. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number Package		Description		Packing quantity			
				3000	4000	8000	10000
PEMH19	SOT666	2 mm pitch, 8 mm tape and reel		-	-	-315	-
	4 mm pitch, 8 mm tape and reel		-	-115	-	-	
PUMH19 SOT363		4 mm pitch, 8 mm tape and reel; T1	[2]	-115	-	-	-135
		4 mm pitch, 8 mm tape and reel; T2	[3]	-125	-	-	-165

[1] For further information and the availability of packing methods, see Section 12.

[2] T1: normal taping

[3] T2: reverse taping

PEMH19; PUMH19

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NPN/NPN resistor-equipped transistors; R1 = 22 k Ω , R2 = open

10. Revision history

Table 10. Revision history

Product data sheet

Document ID	Release date	Data sheet status	Change notice	Supersedes
PEMH19_PUMH19_3	20091115	Product data sheet	-	PEMH19_PUMH19_2
Modifications:	 This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content. 			
	Figure 3 "Pad	ckage outline SOT363 (SC-	88)": updated	
PEMH19_PUMH19_2	20050502	Product data sheet	-	PUMH19_1
PUMH19_1	20031016	Product specification	-	-

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11.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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